

**Features:**

- n Isolated mounting base 3000V~
- n Solder joint technology with increased power cycling capability
- n Space and weight saving

**Typical Applications:**

- n AC/DC Motor drives
- n Various rectifiers
- n DC supply for PWM inverter

$V_{DRM}, V_{RRM}$	Type & Outline
600V	MTC55-06-224H3/224H3B
800V	MTC55-08-224H3/224H3B
1000V	MTC55-10-224H3/224H3B
1200V	MTC55-12-224H3/224H3B
1400V	MTC55-14-224H3/224H3B
1600V	MTC55-16-224H3/224H3B
1800V	MTC55-18-224H3/224H3B

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}\text{C})$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled, $T_c = 85^{\circ}\text{C}$	125			55	A
$I_{T(RMS)}$	RMS on-state current		125			86	A
$I_{DRM}$ $I_{RRM}$	Repetitive peak current	at $V_{DRM}$ at $V_{RRM}$	125			15	mA
$I_{TSM}$	Surge on-state current	10ms half sine wave $V_R = 60\% V_{RRM}$	125			1.7	kA
$I^2t$	$I^2t$ for fusing coordination					14.5	$10^3\text{A}^2\text{s}$
$V_{TO}$	Threshold voltage		125			0.75	V
$r_T$	On-state slope resistance					4.05	$\text{m}\Omega$
$V_{TM}$	Peak on-state voltage	$I_{TM} = 170\text{A}$	25			1.60	V
$dv/dt$	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM}$	125			1000	$\text{V}/\mu\text{s}$
$di/dt$	Critical rate of rise of on-state current	Gate source 1.5A $t_r \leq 0.5\mu\text{s}$ Repetitive	125			200	$\text{A}/\mu\text{s}$
$I_{GT}$	Gate trigger current	$V_A = 12\text{V}, I_A = 1\text{A}$	25	30		200	mA
$V_{GT}$	Gate trigger voltage			0.6		2.5	V
$I_H$	Holding current			10		250	mA
$I_L$	Latching current					1000	mA
$V_{GD}$	Non-trigger gate voltage	$V_{DM} = 67\% V_{DRM}$	125			0.2	V
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled, per chip				0.47	$^{\circ}\text{C}/\text{W}$
$R_{th(c-h)}$	Thermal resistance case to heatsink	Single side cooled, per chip				0.15	$^{\circ}\text{C}/\text{W}$
$V_{iso}$	Isolation voltage	50Hz, R.M.S, $t = 1\text{min}, I_{iso}: 1\text{mA}(\text{MAX})$		3000			V
$F_m$	Thermal connection torque(M5)			2.5		4.0	N·m
	Mounting torque(M6)			4.5		6.0	N·m
$T_{vj}$	Junction temperature			-40		125	$^{\circ}\text{C}$
$T_{stg}$	Stored temperature			-40		125	$^{\circ}\text{C}$
$W_t$	Weight				100		g
Outline	224H3、224H3B						

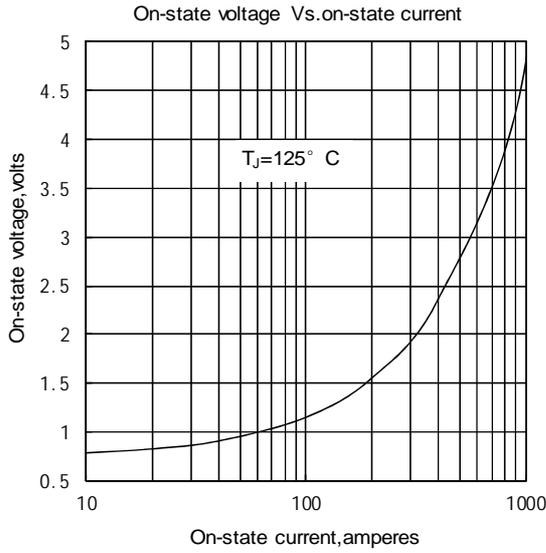


Fig.1

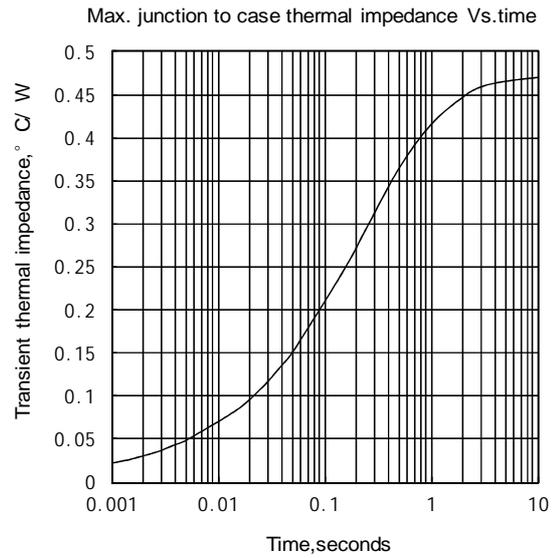


Fig.2

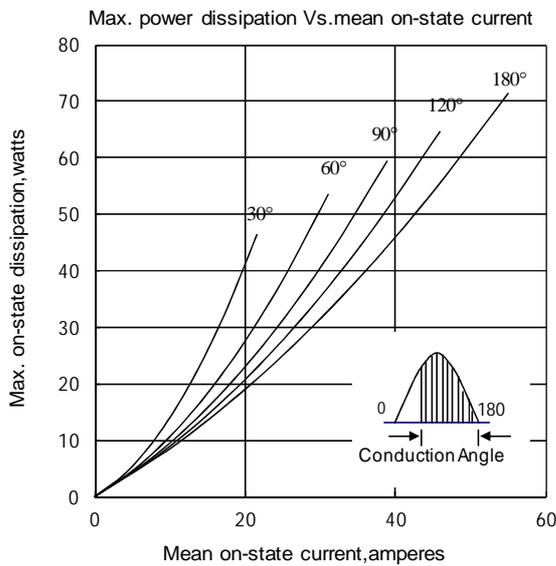


Fig.3

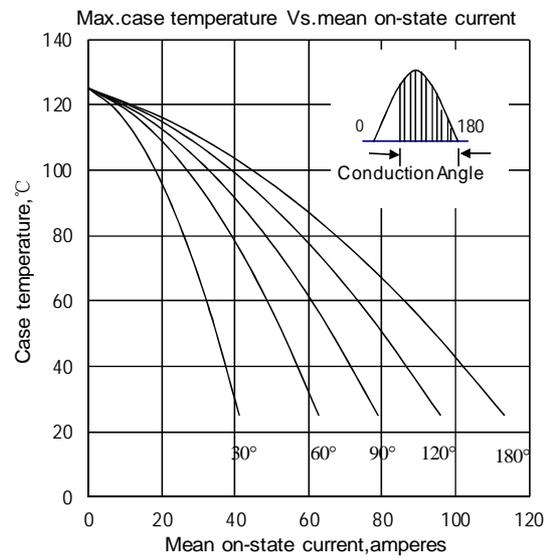


Fig.4

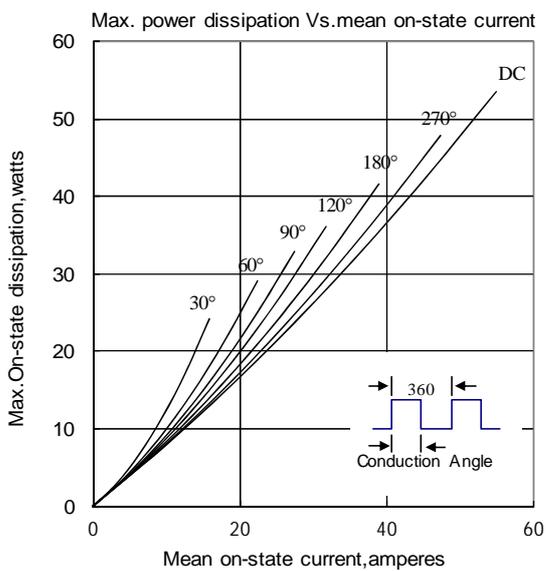


Fig.5

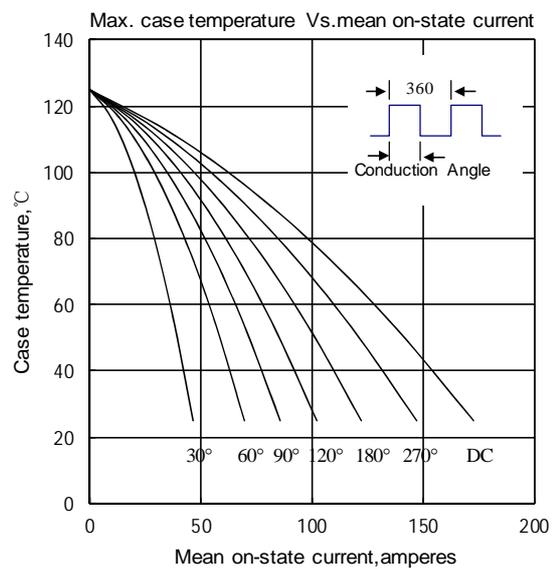


Fig.6

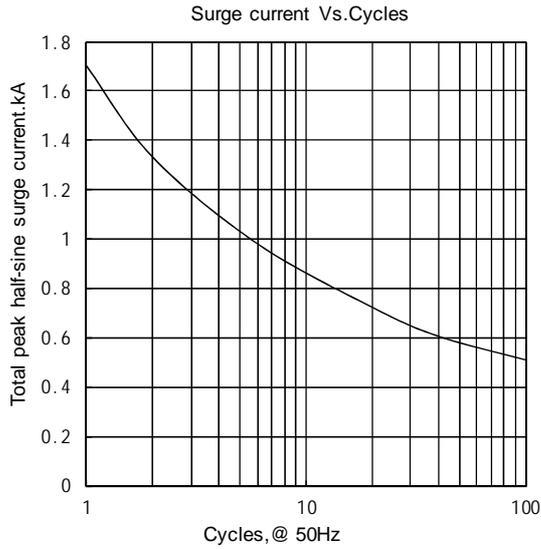


Fig.7

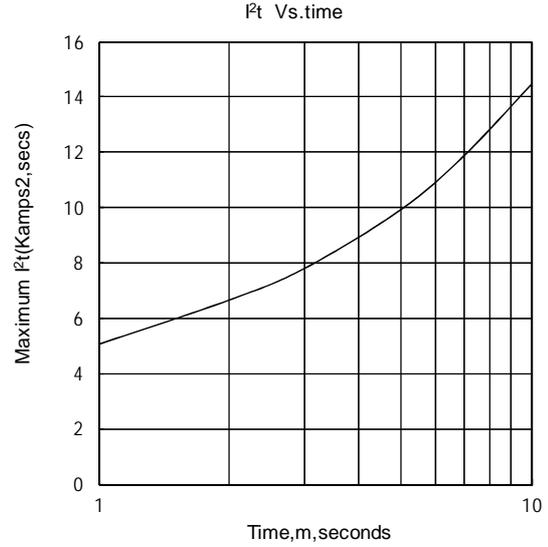


Fig.8

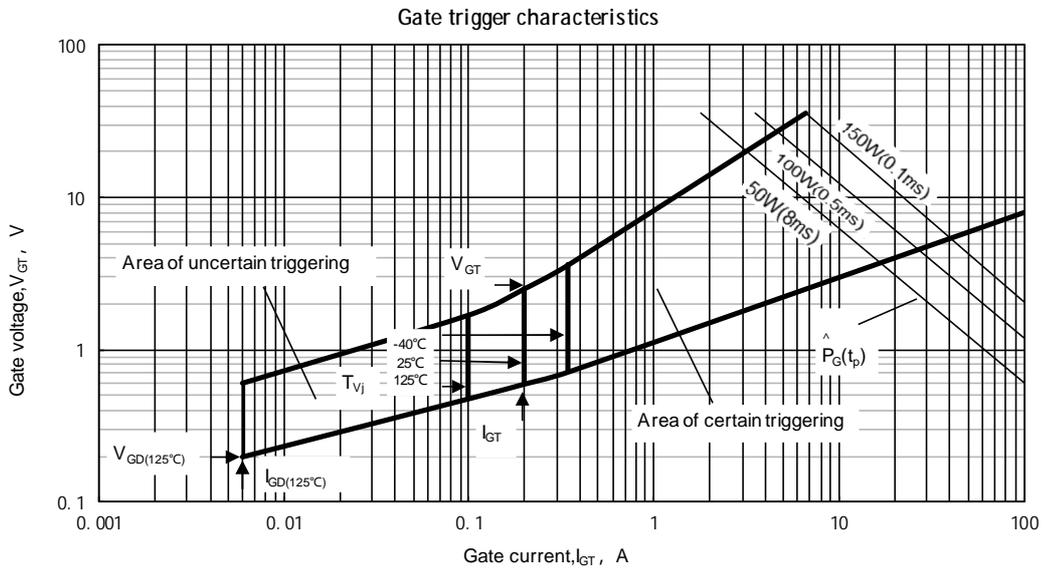
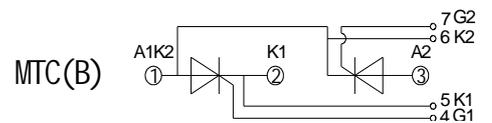
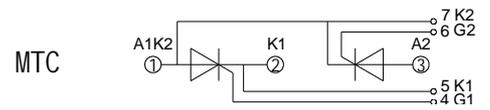
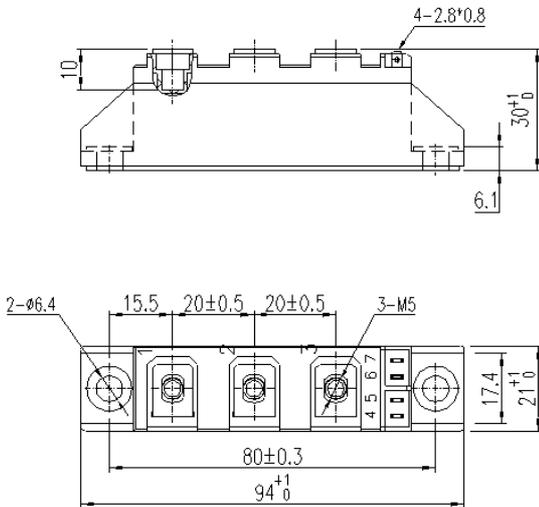


Fig.9

Outline:



Unmarked dimensional tolerance: ±0.5mm

TECHSEM reserves the right to change specifications without notice.